

TOSHIBA Photocoupler GaAlAs Ired + Photo IC

# TLP750

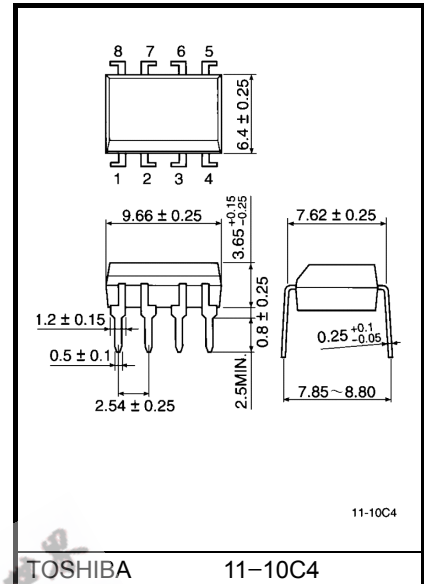
- Digital Logic Ground Isolation
- Line Receiver
- Microprocessor System Interfaces
- Switching Power Supply Feedback Control
- Analog Signal Isolation

The TOSHIBA TLP750 consists of GaAlAs high-output light emitting diode and a high speed detector of one chip photo diode-transistor. This unit is 8-lead DIP.

TLP750 has no internal base connection, and is suitable for application in noisy environmental conditions.

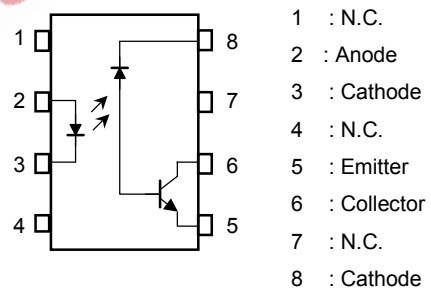
- Switching speed:  $t_{pHL}=0.3\mu s$ (typ.)
  - Switching speed:  $t_{pLH}=0.5\mu s$ (typ.)( $R_L=1.9k\Omega$ )
  - UL recognized: UL1577, file No. E67349
  - BSI approved: BS EN60065: 2002,  
Certificate No.8869  
BS EN60950-1: 2002,  
Certificate No.8870
  - Isolation voltage:  $5000V_{rms}$ (min.)
  - Option(d4)type  
VDE approved: DIN EN 60747-5-2,  
Certificate No. 40009302  
Maximum operating insulation voltage:  $890V_{PK}$   
Highest permissible over voltage:  $8000V_{PK}$
- (Note) When a EN 60747-5-2 approved type is needed, please designate the "Option(D4)"**
- Creepage distance: 6.4mm(min.)  
Clearance: 6.4mm(min.)  
Insulation thickness: 0.4mm(min.)

Unit in mm

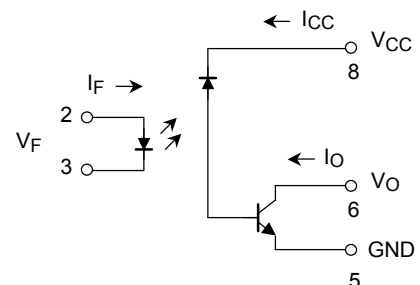


Weight: 0.54g

### Pin Configuration (top view)



### Schematic



## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current (Note 1)	I <sub>F</sub>	25	mA
	Pulse forward current (Note 2)	I <sub>FP</sub>	50	mA
	Peak transient forward current (Note 3)	I <sub>FPT</sub>	1	A
	Reverse voltage	V <sub>R</sub>	5	V
	Diode power dissipation (Note 4)	P <sub>D</sub>	45	mW
Detector	Output current	I <sub>O</sub>	8	mA
	Peak output current	I <sub>OP</sub>	16	mA
	Output voltage	V <sub>O</sub>	-0.5~15	V
	Supply voltage	V <sub>CC</sub>	-0.5~15	V
	Output power dissipation (Note 5)	P <sub>O</sub>	100	mW
Operating temperature range		T <sub>opr</sub>	-55~100	°C
Storage temperature range		T <sub>stg</sub>	-55~125	°C
Lead solder temperature(10s) (Note 6)		T <sub>sol</sub>	260	°C
Isolation voltage (AC, 1min., R.H=60%) (Note 7)		BV <sub>S</sub>	5000	V <sub>rms</sub>

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Derate 0.8mA / °C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width.  
Derate 1.6mA / °C above 70°C.

(Note 3) Pulse width ≤ 1μs, 300pps.

(Note 4) Derate 0.9mW / °C above 70°C.

(Note 5) Derate 2mW / °C above 70°C.

(Note 6) Soldering portion of lead: Up to 2mm from the body of the device.

(Note 7) Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together and pins 5, 6, 7 and 8 shorted together.

## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition		Min.	Typ.	Max.	Unit	
LED	Forward voltage	$V_F$	$I_F=16\text{mA}$		—	1.65	1.85	V	
	Forward voltage temperature coefficient	$\Delta V_F / \Delta T_a$	$I_F=16\text{mA}$		—	-2	—	mV / °C	
	Reverse current	$I_R$	$V_R=5\text{V}$		—	—	10	$\mu\text{A}$	
	Capacitance between terminal	$C_T$	$V_F=0, f=1\text{MHz}$		—	45	—	pF	
Detector	High level output current	$I_{OH(1)}$	$I_F=0\text{mA}, V_{CC}=V_O=5.5\text{V}$		—	3	500	nA	
		$I_{OH(2)}$	$I_F=0\text{mA}, V_{CC}=V_O=15\text{V}$		—	—	5	$\mu\text{A}$	
		$I_{OH}$	$I_F=0\text{mA}, V_{CC}=V_O=15\text{V}$ $T_a=70^\circ\text{C}$		—	—	50	$\mu\text{A}$	
	High level supply voltage	$I_{CCH}$	$I_F=0\text{mA}, V_{CC}=15\text{V}$		—	0.01	1	$\mu\text{A}$	
Coupled	Current transfer ratio	$I_O/I_F$	$I_F=16\text{mA}$ $V_{CC}=4.5\text{V}$ $V_O=0.4\text{V}$	$T_a=25^\circ\text{C}$	10	30	—	%	
				Rank: 0	19	30	—		
				$T_a=0\sim 70^\circ\text{C}$	5	—	—		
	Low level output voltage	$V_{OL}$	$I_F=16\text{mA}, V_{CC}=4.5\text{V},$ $I_O=1.1\text{mA}$ (rank 0: $I_O=2.4\text{mA}$ )			—	—	0.4	V
						—	—	—	
Isolation resistance	$R_S$	R.H.=60%, $V=5000\text{V}_{\text{DC}}$		(Note 7)	$1 \times 10^{12}$	$10^{14}$	—	$\Omega$	
Capacitance between input to output	$C_S$	$V_S=0, f=1\text{MHz}$		(Note 8)	—	0.8	—	pF	

## Switching Characteristics (Ta = 25°C, VCC = 5V)

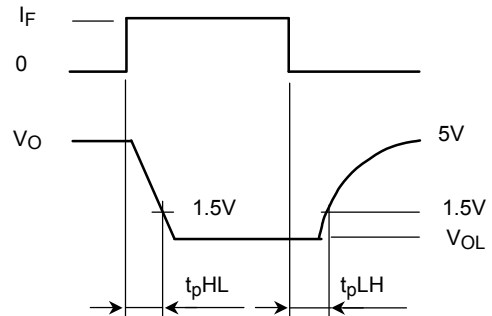
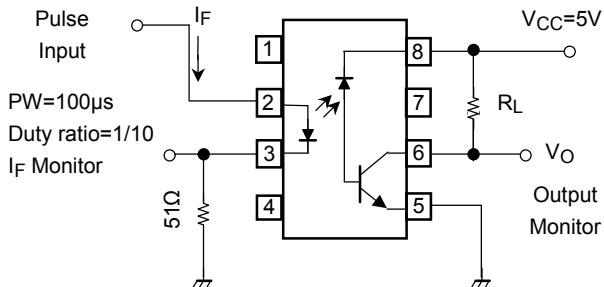
Characteristic	Symbol	Test Circuit	Test Condition	Min.	Typ.	Max.	Unit
Propagation delay time (H→L)	$t_{pHL}$	1	$I_F=0 \rightarrow 16\text{mA}, V_{CC}=5\text{V},$ $R_L=4.1\text{k}\Omega$	—	0.2	0.8	$\mu\text{s}$
			Rank 0: $R_L=1.9\text{k}\Omega$	—	0.3	0.8	
Propagation delay time (L→H)	$t_{pLH}$	1	$I_F=16 \rightarrow 0\text{mA}, V_{CC}=5\text{V},$ $R_L=4.1\text{k}\Omega$	—	1.0	2.0	$\mu\text{s}$
			Rank 0: $R_L=1.9\text{k}\Omega$	—	0.5	1.2	
Common mode transient immunity at logic high output (Note 8)	$C_{MH}$	2	$I_F=0\text{mA}, V_{CM}=200\text{V}_{\text{p-p}}$ $R_L=4.1\text{k}\Omega$ (Rank 0: $R_L=1.9\text{k}\Omega$ )	—	1500	—	V / $\mu\text{s}$
Common mode transient immunity at logic low output (Note 8)	$C_{ML}$		$I_F=16\text{mA}, V_{CM}=200\text{V}_{\text{p-p}}$ $R_L=4.1\text{k}\Omega$ (Rank 0: $R_L=1.9\text{k}\Omega$ )	—	-1500	—	V / $\mu\text{s}$

(Note 8) CML is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state ( $V_O < 0.8V$ ).

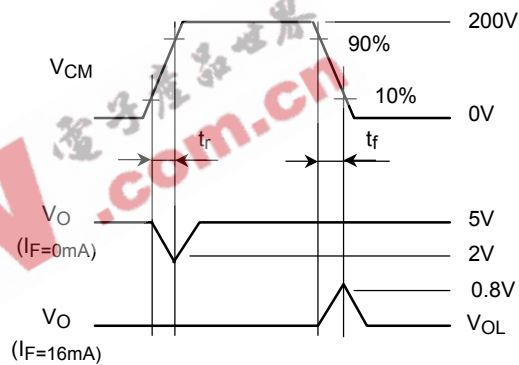
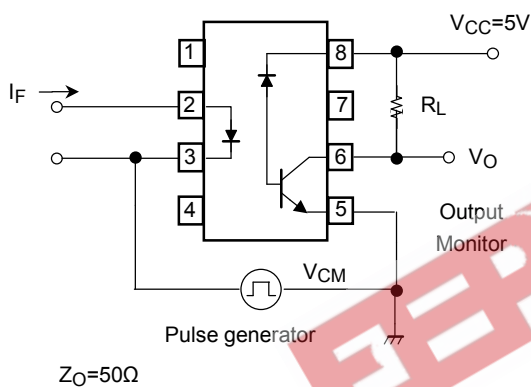
CMH is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state ( $V_O > 2.0V$ ).

(Note 9) Maximum electrostatic discharge voltage for any pins: 100V(C=200pF, R=0)

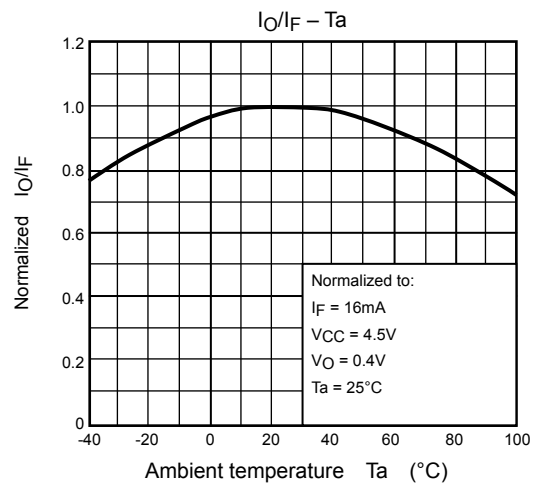
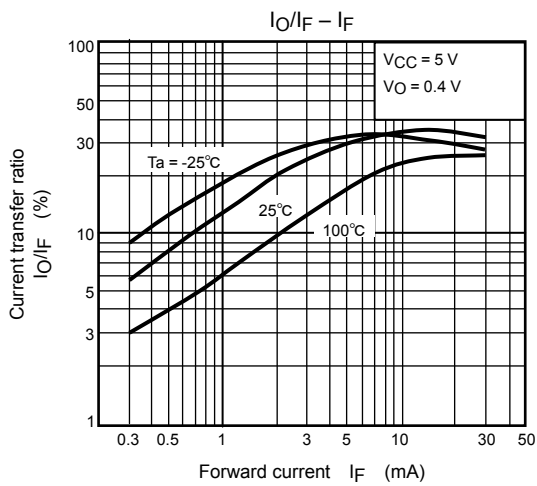
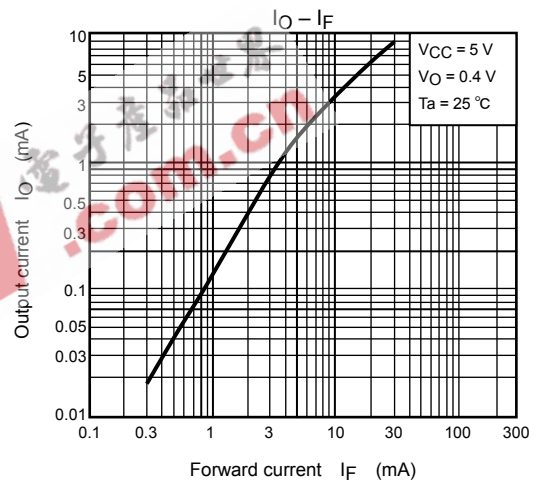
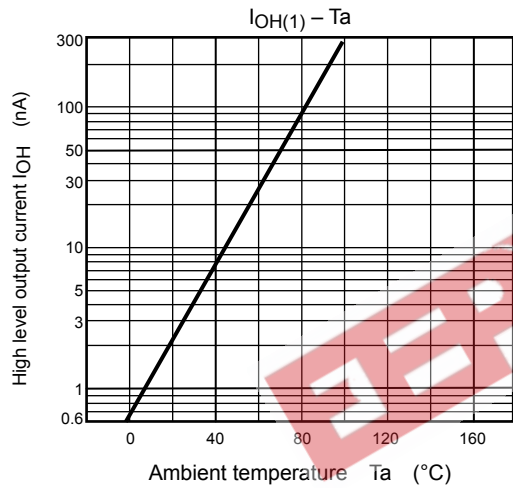
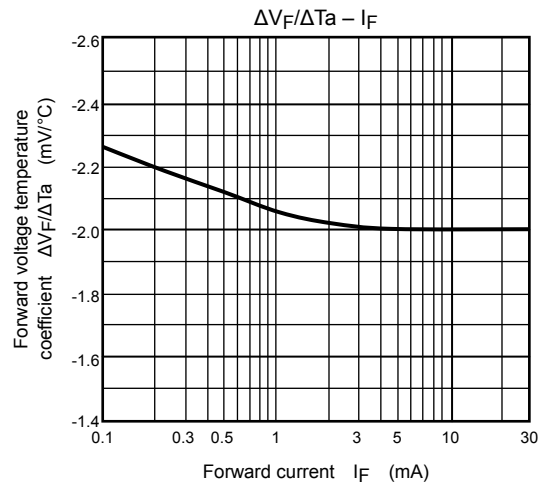
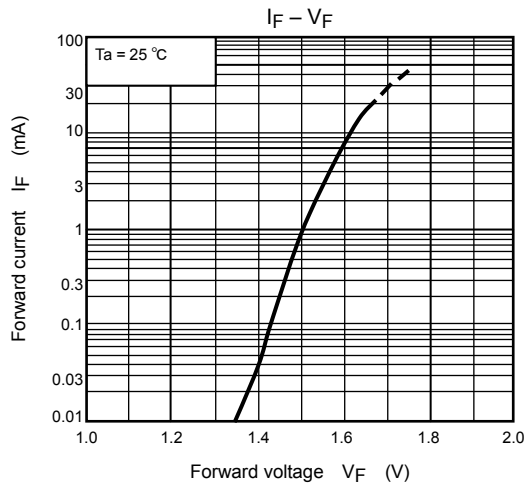
## Test Circuit 1: Switching Time Test Circuit

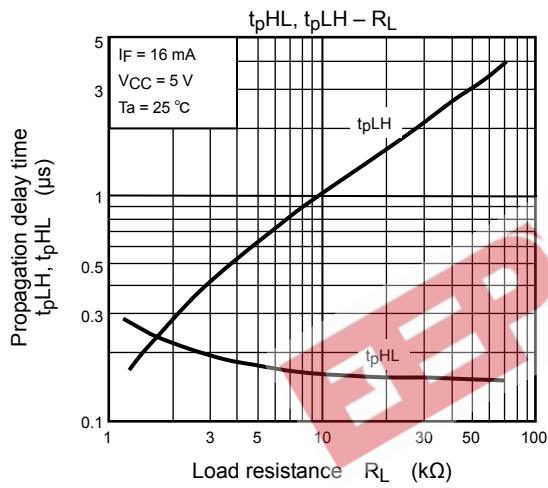
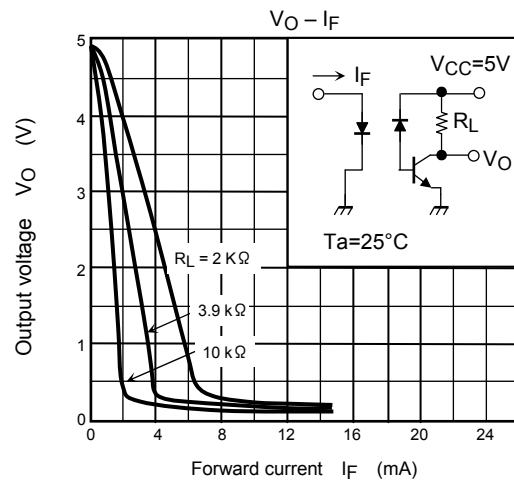
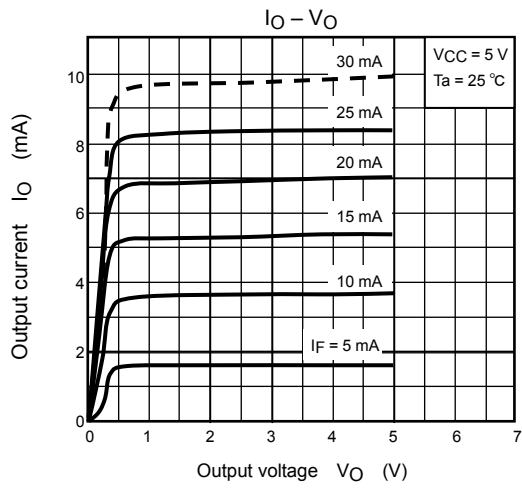


## Test Circuit 2: Common Mode Noise Immunity Test Circuit



$$CM_H = \frac{160(V)}{t_r(\mu s)}, CM_L = \frac{160(V)}{t_f(\mu s)}$$





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